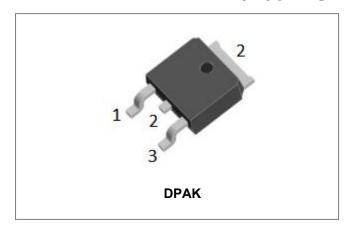






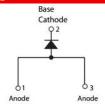
## MBRD20100-H SCHOTTKY RECTIFIER



#### **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- "-A" is an AEC-Q101 qualified device
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

## **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Rectified Forward Current	l <sub>F (AV)</sub>	50% duty cycle @Tc=105°C, rectangular wave form	20	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse	100	Α

## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 20A, Pulse, T <sub>J</sub> = 25 °C	0.80	0.88	V
	V <sub>F2</sub>	@ 20A, Pulse, T <sub>J</sub> = 125 °C	0.70	0.74	V
Reverse Current *	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.006	1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	0.1	6.0	mA
Junction Capacitance	Ст	$@V_R = 5.0V, T_C = 25 °C$ $f_{SIG} = 1MHz$	380	400	pF

 $<sup>^*</sup>$  Pulse width < 300  $\mu$ s, duty cycle < 2%



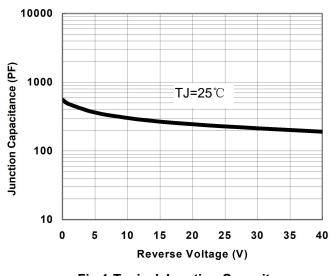




## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	-	2	°C/W
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

## **Ratings and Characteristics Curves**



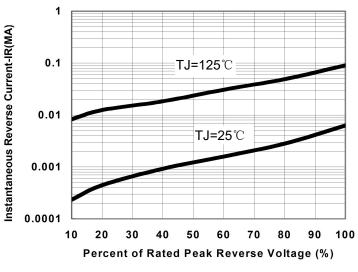


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

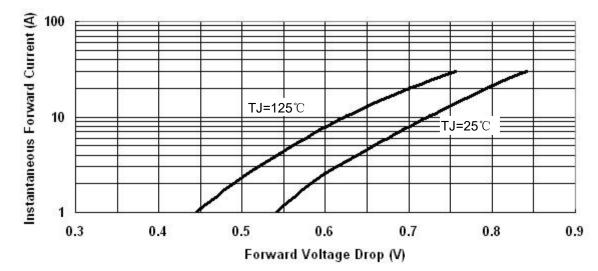


Fig.3-Typical Instantaneous Forward Voltage Characteristics

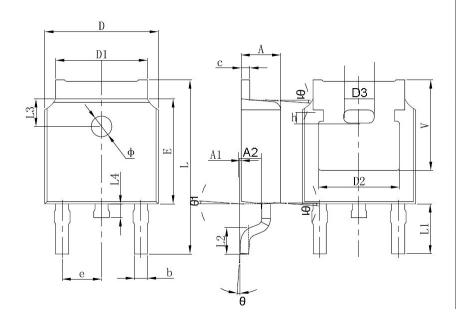
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## **Mechanical Dimensions DPAK**



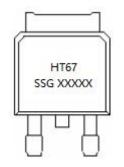
SYMBOL	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
А	2.20	2.40	0.087	0.094	
A1	0.00	0.127	0.000	0.005	
b	0.66	0.86	0.026	0.034	
С	0.46	0.60	0.018	0.024	
D	6.50	6.70	0.256	0.264	
D1	5.13	5.46	0.202	0.215	
D2	4.83	REF.	0.190 REF.		
Е	6.00	6.20	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.70	10.40	0.381	0.409	
L1	2.90 REF.		0.144 REF.		
L2	1.40	1.70	0.055	0.067	
L3	1.60 REF.		0.063 REF.		
L4	0.60	1.00	0.024	0.039	
Ф	1.10	1.30	0.043	0.051	
Θ	0°	8°	0°	8°	
h	0.00	0.30	0.000	0.012	
V	5.35 REF.		0.211	REF.	

## **Ordering Information**

Device	Package	Shipping
MBRD20100-H	DPAK (Pb-Free)	2500pcs / reel
MBRD20100TR-H	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



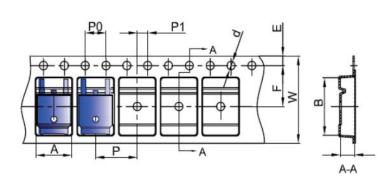
Where XXXXX is YYWWL

HT67 = Marking Code
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

## **Carrier Tape Specification DPAK**



SYMBOL	Millimeters		
STWIDGE	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Ф1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

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